

09/750,116
WAK.071

a photo-acid generator for generating an acid by exposure.

5. (Amended) A photoresist material comprising:
the polymer according to claim 3; and
a photo-acid generator for generating an acid by exposure.

6. (Amended) A photoresist material according to claim 4, further comprising:
a polyhydric alcohol.

7. (Amended) A photoresist material according to claim 5, further comprising:
a polyhydric alcohol.

8. (Amended) A photoresist composition, comprising:
70 to 99.8% by weight of the polymer according to claim 2; and
0.2 to 30% by weight of a photo-acid generator for generating an acid by exposure.

9. (Amended) A photoresist composition, comprising:
70 to 99.8% by weight of the polymer according to claim 3; and
0.2 to 30% by weight of a photo-acid generator for generating an acid by exposure.

10. (Amended) A method for forming a pattern, comprising:
applying the photoresist material according to claim 4 onto a substrate to be worked;
exposing the material to a light having a wavelength of 180 to 220 nm;
baking said material; and
selectively dissolving one of an exposed portion and an unexposed portion of said material to develop said pattern.

11. (Amended) A method for forming a pattern, comprising:
applying the photoresist material according to claim 5 onto a substrate to be worked;

09/750,116
WAK.071

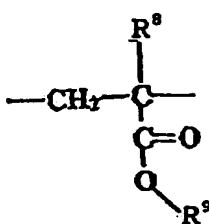
exposing the material to a light having a wavelength of 180 to 220 nm;
baking said material; and
selectively dissolving one of an exposed portion and an unexposed portion of said
material to develop said pattern.

12. (Amended) The method for forming the pattern according to claim 10 wherein said
light comprises an ArF excimer laser light.

13. (Amended) The method for forming the pattern according to claim 11 wherein said
light comprises an ArF excimer laser light.

16. (Amended) A polymer which is obtained by polymerizing the (meth) acrylate
derivative according to claim 15, or copolymerizing the (meth) acrylate derivative according
to claim 15 with another polymerizable compound and has a weight-average molecular
weight of 2000 to 200000.

17. (Amended) A resin for resist having a solubility to an alkaline aqueous solution which
increases due to the decomposition of an acid-decomposable group thereof by an action of an
acid, said resin comprising a (meth)acrylate unit of an alicyclic lactone structure represented
by the formula (3):



(3)

wherein R⁸ is a hydrogen atom or a methyl group, and R⁹ is a hydrocarbon group of 7 to 16
carbon atoms having an alicyclic lactone structure.

09/750,116
WAK.071

18. (Amended) The resin for resist according to claim 17, wherein said resin comprises the polymer according to one of claim 2 or claim 14.

19. (Amended) A photoresist material comprising:
the polymer according to one of claims 14 or 16; and
a photo-acid generator for generating an acid by exposure.

20. (Amended) The photoresist material according to claim 19, further comprising:
a polyhydric alcohol.

21. (Amended) A photoresist composition comprising:
70 to 99.8% by weight of the polymer according to one of claims 17 or 18; and
0.2 to 30% by weight of a photoacid generator for generating an acid by exposure.

22. (Amended) A method for forming a pattern comprising:
applying the photoresist composition according to claim 21 onto a substrate to be worked;
exposing the composition to a light having a wavelength of 180 to 220 nm;
baking said material; and
selectively dissolving one of an exposed portion and an unexposed portion of said material to develop said pattern.

23. (Amended) The method for forming the pattern according to claim 22, wherein said light comprises an ArF excimer laser light.